



DC 3-phase Brushless Motor Driver (Output Current 3A)

[STK6103]

Package Dimensions

unit: mm

2-\$3.6

4130

Overview

The STK6103 is a hybrid IC incorporating a 3-phase brushless motor controller and driver into a single package, on the Sanyo IMST (Insulated Metal Substrate Technology) substrate. Revolution speed is controlled through the DC voltage level (Vref₁) external input and PWM control of motor phase winding current. The driver is MOSFET to minimize circuit loss and handle high-output current (rush current) demands.

Applications

- PPC and LBP drum motors
- Air conditioner fan motors

Features

- The output driver transistor is MOSFET for low power loss hand
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- Nor
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- Curi

Specifications

Maximum Ratings at $Ta = 25^{\circ}C$

es (half that of a bipolar transistor) and reliable adding of high-output current (rush current).	(8) 27X2=54 2.9	
riation in Vref ₁ level causes the driver transistor to itch to PWM drive for high-efficiency motor speed riation.		
ormal and reverse revolution select function.		
art/stop and brake functions.		
rrent limiter function.		

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage 1	V _{cc} 1 max	No input signal	50	V
Maximum supply voltage 2	V _{CC} 2 max	No input signal	7	V
Maximum output current	I _o max	Position detect input signal cycle = 30 ms, PWM duty = 50%, operation time 1s	5	А
Operating substrate temperature	T _c max		105	ů
Junction temperature	T _j max		150	°C
Storage temperature	Tstg		-40 to +125	°C

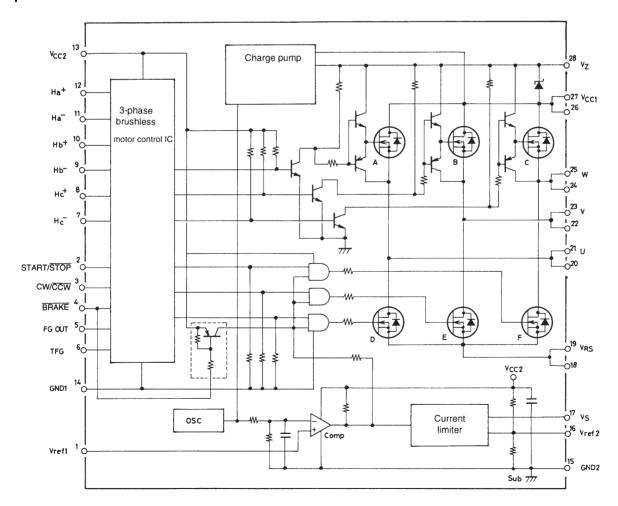
Allowable Operating Ranges at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions Ratings		Unit
Supply voltage 1	V _{cc} 1	With input signal	16 to 42	V
Output current	lo ave	DC phases present	3	Α
Supply voltage 2	V _{CC} 2	With input signal	4.75 to 6.0	V
Brake current	I _{OB}	80 Hz full sine waves (all phases). Operating time 0.1 s duty = 5% (see Note 1).	8	А

Electrical Characteristics at $Tc{=}25^{\circ}C,\,V_{\rm CC}1$ = 24 $V,\,V_{\rm CC}2$ = 5.0 V

Parameter	Symbol	Conditions	min	typ	max	Unit
Supply current 1 (pin 13)	I _{cco} 1	CW revolution		12	20	mA
Supply current 2 (pin 13)	I _{cco} 2	Braking		26	38	mA
Output saturation voltage 1	Vst1	V _{CC} 1 side TR, Io = 3A		0.43	0.56	V
Output saturation voltage 2	Vst2	GND side TR, Io = 3A		0.47	0.62	V
Internal MOSFET diode forward voltage	V _F	I _F = 3A		0.95	1.5	V
PWM oscillation frequency	f _C		20	25	30	kHz
Current limiter reference voltage	Vref2		0.47	0.50	0.53	V
Position detect input sensitivity	V _H		20		500	mV
Position detect common mode range	CMRH		2.0		4.5	V
Input "L" current 1 (pins 2,3)	I _{IL1}	V _{IL1} = GND		130	200	μΑ
Input "L" voltage 1 (pins 2,3)	V _{IL1}				1.0	V
Input "L" current 2 (pin 4)	I _{IL2}	V _{IL2} = GND		570	910	μA
Input "L" voltage 2 (pin 4)	V _{IL2}				1.0	V
Vref1 "H" voltage	Vref _{1H}	GND side transistor not in PWM		2.82	3.2	V
Vref1 "L" voltage	Vref _{1L}	GND side transistor off	0.15	0.35		V
Zener voltage	V _z		5.7	6.2	6.7	V
FG output current	I _{FGH}	V _{FG} = 1.6 V	80			μA
FG output "L" voltage	V _{FGL}	I _{FG} = 0.3 mA			0.4	V
FG output pulse width	τ_{FG}	$C_F = 0.1 \mu F, R_F = 10 \text{ k}\Omega$	0.9	1.0	1.1	ms

Equivalent Circuit

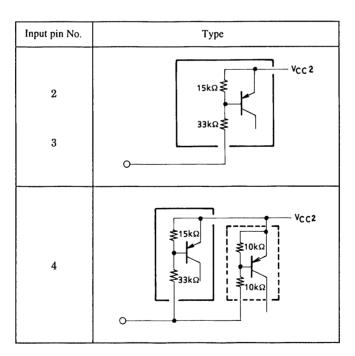


STK6103

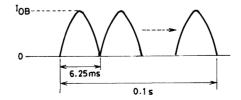
Pin Functions

Pin No.	Symbol	Function
1	Vref₁	GND-side driver transistor PWM control pin: range 0.15 to 3.2V
2	START/STOP	"H" = START, "L" = $\overline{\text{STOP}}$ (all transistors off)
3	CW/CCW	"H" = CW, "L" = CCW
4	BRAKE	"H" = rotate, "L" = Only GND-side transistor on
5	FG OUT	Position detect signal: output 6 pulses per cycle
6	TFG	For setting FG OUT "L" level pulse width. R _F and C _F pins.
7	H _{c-}	Motor position detect signal input pin (to Hall device)
8	H _{C+}	Motor position detect signal input pin (to Hall device)
9	H _{b-}	Motor position detect signal input pin (to Hall device)
10	H _{b+}	Motor position detect signal input pin (to Hall device)
11	H _a _	Motor position detect signal input pin (to Hall device)
12	H _{a+}	Motor position detect signal input pin (to Hall device)
13	V _{cc} 2	Motor controller supply voltage pin
14	GND1	Motor controller IC GND pin: signal ground (SG)
15	GND2	External R _s GND-side connection pin: power ground (PG)
16	Vref ₂	Current limiter set pin: 0.1V _{cc} 2 when open
17	V _s	External R _s current limiter detect pin
18, 19	V _{RS}	External R _s connect pin
20, 21	U	Output pin (to motor winding)
22, 23	V	Output pin (to motor winding)
24, 25	W	Output pin (to motor winding)
26, 27	V _{cc} 1	Supply voltage pin (to motor)
28	VZ	Zener voltage (6.2V typ) for V _{cc} 1 driver transistor date source supply

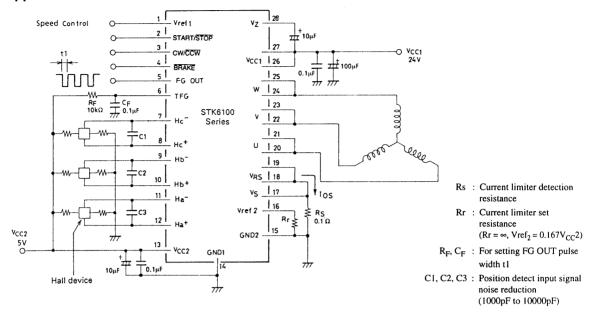
Input Type



Note 1: I_{OB} indicates the operating current waveform peak as shown below.



Sample Application Circuit



Description of Operation

The DC 3-phase brushless motor generally uses a permanent magnet for the rotor and places the stator coil around it. When the rotor and stator coil are excited, magnetic force is generated between the poles, which is used for revolution torque. For efficient revolution it is necessary to know precisely where the rotor pole is in relation to the stator pole. In the brushless motor Hall devices and Hall ICs are widely used for this purpose, by detecting the electric power generated along the lines of magnetic force.

(1) Motor rotating force

The block diagram for this HIC is given in Fig. 2.

The conditions before input of $V_{\rm CC}1$, with $V_{\rm CC}2$ on, are START/STOP pin H level, CW/CCW pin H level, $\overline{\rm BRAKE}$ pin H level and ${\rm Vref}_1$ pin (speed control input) H level. The position detect signal at this time, due to the effect of the rotor magnetic field, will be output signals from 1 or 2 devices (of the 3) so that $H_{\rm X+} > H_{\rm X-}$ is input to HIC pins 7 to 12. The signals input to pins 7 to 12 are input to the motor controller and converted into signals compatible with 3-phase brushless motor revolution. When $V_{\rm CC}1$ is supplied the charge pump circuit activates, generating $V_{\rm CC}1$ MOSFET gate voltage $V_{\rm Z}$. This outputs excitation current to the motor phase windings as indicated in the timing chart (Fig. 3), and rotating the motor.

For revolution speed control, the Vref₁ pin voltage is converted and used for PWM drive to increase GND transistor efficiency, controlling the conduction of motor current Io (Fig. 1). Control of Io means control of power supplied to the motor, which controls motor rpm. In general motor rpm N is proportional to the PWM on duty (when motor load is constant). The PWM on duty is proportional to the size of Vref₁ (see Fig. 13), and the relation of N is as outlined below.

$$N \propto PWM ON Duty \propto Vref_1$$

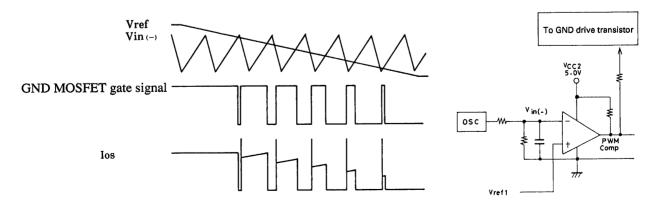


Fig.1 PWM Drive Principle

Motor revolution is stopped by setting $START/\overline{STOP}$ to L level to turn off all drive transistors, and cut the supply of current to the motor. Motor inertia will prevent instantaneous stopping. The brake function works to shorten the amount of time needed to come to a complete stop. In input level L the $V_{CC}1$ driver transistor is turned off, all GND driver transistors are turned on, and the amount of power generated by the rotating motor windings reduced to reduce the rpms. This brake function has priority over all $START/\overline{STOP}$, CW/\overline{CCW} and position detect input conditions.

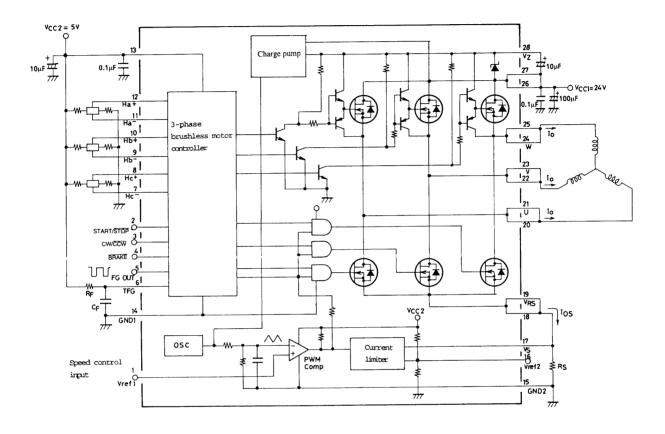


Fig. 2 Block Diagram

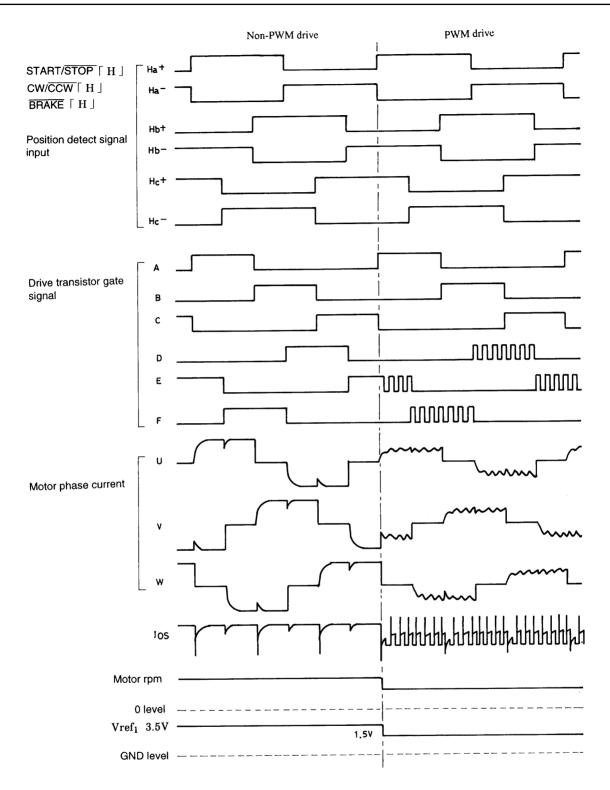


Fig. 3 I/O Timing Chart

(2) Other functions

① CW/CCW

The direction of motor revolution can be selected by setting the input level to H or L. CW is H level and \overline{CCW} is L level. The CW timing chart is indicated in Fig. 3, and the \overline{CCW} timing chart in Fig. 5.

2 Current limiter function

The current limiter converts the GND driver transistor source current into V_{RS} through the external R_{S} , and controls GND driver transistor conduction based on a comparison of this voltage to $Vref_2$. $Vref_2$ generates a 0.1 V_{CC}^2 voltage in pin open state. $Vref_2$ is generated by the voltage division between 27 k Ω and 3 k Ω resistances, and so the $Vref_2$ level can be readily reduced by attaching an external resistor. To prevent HIC destruction in the event of motor lock, a current limiter can be enabled by setting $Vref_2$ at or below Io ave. If no such protection is required, set $Vref_2$ between Io max and Io ave to limit rush current.

③ FG OUT

This pin outputs a square wave pulse proportional to one motor revolution, which can be used as the motor servo-control PLL IC FG input signal. The square wave L level time t_1 is set by the time constant of C_F and R_F connected to the TFG pin (Fig. 4).

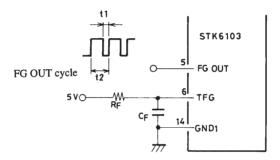


Fig. 4

In general, when the n-pole 3-phase brushless motor fixed-speed rpm is expressed as N(rpm), the setting for t_1 so that $t_1 = 0.5$ t_2 is given by expression ①.

$$t_1 = \frac{1000}{\frac{N}{60} \times 6 \times \frac{n}{2}} \times 0.5 \text{ [ms]} \dots$$

The relation between C_F , R_F and t_1 is given by expression @.

$$t_1 \approx a \cdot R_F \cdot C_F$$
 2

However,
$$a = 1$$
 $\left(\frac{s}{\Omega \cdot F}\right)$, $R_F = 3 \text{ k}\Omega$ to $30 \text{ k}\Omega$, $t_1 > 50 \text{ µs}$

Expression ① is designed to be half that of fixed speed t_2 , but when an FV conversion circuit is connected to the FG OUT pin, it is necessary to reduce the duty to under 50%. In this case, adjust R_F or C_F as needed.

(3) Precautions in drive

① Start current (rush current)

The motor start Rs current waveform is shown in Fig. 6. Current peak I_{OH} must not exceed Io max.

② Position detect signal

Because signal input sensitivity V_H is ± 500 mV max, the level of the output signal (open collector) from the Hall IC must be reduced through conversion. A sample of this circuit is shown in Fig. 7. The position detect signal must be compatible with the motor phase winding even in the time chart state shown in Fig. 3, or the motor may not revolve smoothly.

3 Motor phase winding current during braking

The motor phase winding current during braking must not exceed Io max even during peak, although several times set current levels are input.

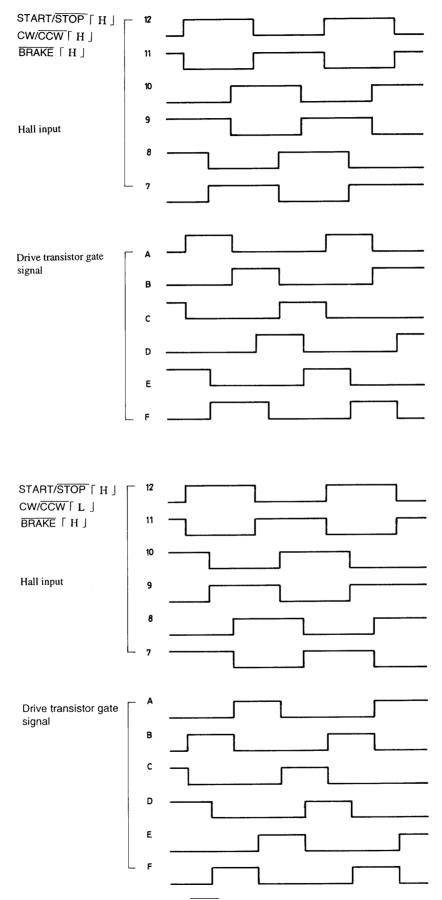


Fig. 5 CW/CCW I/O Timing Chart

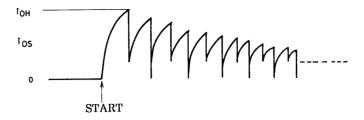


Fig.6 Starting Current

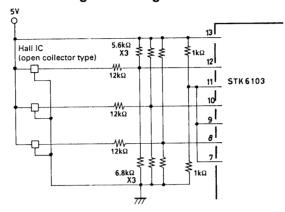


Fig.7 Conversion Circuit for Hall IC and Hall Device Signal

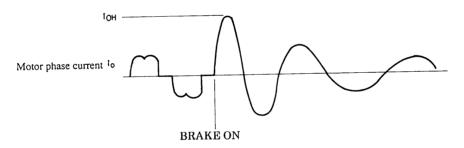


Fig.8

Thermal Radiation Design

(1) Internal average power dissipation Pd

The driver transistors represent the majority of the power dissipation in operation. Other losses are $V_{\rm CC}2$ and the charge pump circuit. In PWM drive in particular, the diode in the $V_{\rm cc}1$ transistor is being used as a flywheel diode, increasing $V_{\rm CC}1$ transistor loss. When these are included, internal mean power dissipation is:

$$\begin{split} Pd &= Io\;(Vst_1 + V_Fd_2 + Vst_2d_1) + Pd_A + Pd_B + Pd_C & \cdots \\ &Io &: Motor\; current \\ &Vst_1 : V_{CC}1 \; transistor\; saturation\; voltage \\ &Vst_2 : GND\; transistor\; saturation\; voltage \\ &d_1 : GND\; transistor\; PWM\; operation\; on\; duty \end{split}$$

: GND transistor PWM operation off duty

 $\begin{array}{l} Pd_A : V_{CC}2 \; loss \\ Pd_B : Charge \; pump \; circuit \; loss \\ Pd_C : GND \; transistor \; switching \; loss \\ V_F : V_{CC}1 \; transistor \; internal \; diode \; normal \; direction \; voltage \end{array}$

Because the driver transistor is a MOSFET, Vst₁ and Vst₂ will increase with an increase in I₀ or substrate temperature Tc.

Pd_A and Pd_B are generally given as:

$$\begin{array}{l} Pd_{_{A}} \approx V_{_{CC}}2 \text{ x } I_{_{CCO1}} \cdots & \textcircled{2} \\ Pd_{_{B}} \approx V_{_{CC}}1 \text{ x } (0.49V_{_{CC}}1-4.2) \text{ x } 0.001 \cdots & \textcircled{3} \\ \end{array}$$

where,
$$V_{CC}1 = 16$$
 to $42V$

Refer to Figs. 11 to 14 for data on Vst_1 , Vst_2 , d_1 and V_F .

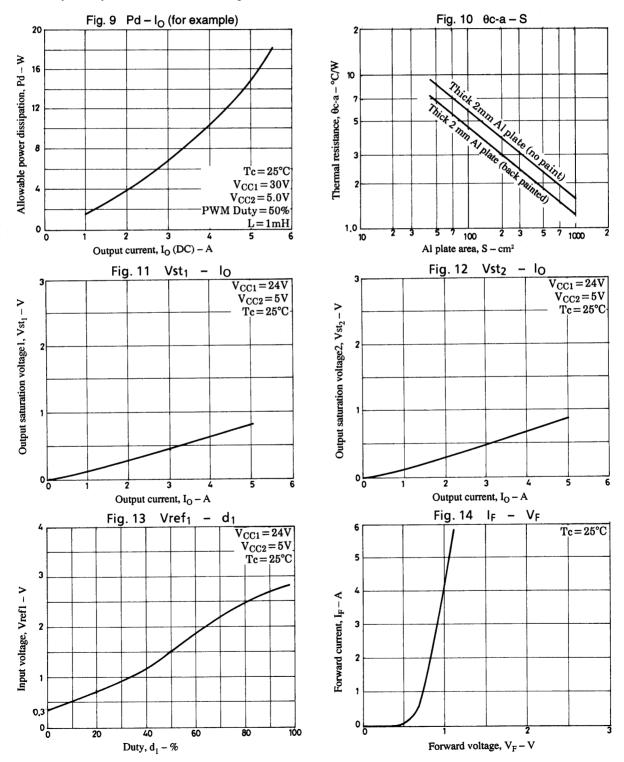
(2) Thermal radiation design

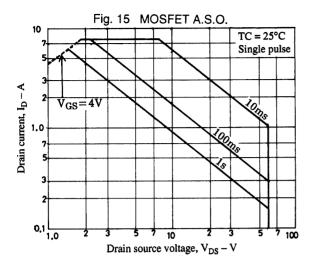
Actual thermal radiation design requires determination of the IC internal average power dissipation Pd from the motor phase current Io (Fig. 9). Pd is then used to determine the thermal resistance for the radiator from the following expression.

$$\theta c - a = \frac{Tc \ max - Ta}{Pd} \ (^{\circ}C/W)$$

where $Tc max = 105^{\circ}C$ Ta = ambient temperature

With a 2.0 mm radiation plate, the required area can be determined from Fig. 10. Note that substrate temperature will vary widely with set internal air temperature, and Tc for the mounted state must be 105°C max.





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